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The structure of the polar Sn-doped indium oxide (001) surfa

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#	Paper	IF	Citations
35	Surface energies control the self-organization of oriented In2O3 nanostructures on cubic zirconia. <i>Nano Letters</i> , 2010 , 10, 3740-6	11.5	90
34	Nucleation of islands and continuous high-quality In2O3(001) films during plasma-assisted molecular beam epitaxy on Y-stabilized ZrO2(001). <i>Journal of Applied Physics</i> , 2010 , 107, 113519	2.5	38
33	Tilting during island growth of In2O3 on Y-stabilized ZrO2(001) revealed by high-resolution x-ray diffraction. <i>Physical Review B</i> , 2010 , 82,	3.3	11
32	Wafer-Scale Growth of ITO Nanorods by Radio Frequency Magnetron Sputtering Deposition. Journal of the Electrochemical Society, 2011 , 158, K131	3.9	29
31	Electronic basis of visible region activity in high area Sn-doped rutile TiO2 photocatalysts. <i>Physical Chemistry Chemical Physics</i> , 2011 , 13, 7882-91	3.6	44
30	UV light emitting transparent conducting tin-doped indium oxide (ITO) nanowires. <i>Nanotechnology</i> , 2011 , 22, 195706	3.4	93
29	Effect of surface roughness and surface modification of indium tin oxide electrode on its potential response to tryptophan. <i>Electrochimica Acta</i> , 2011 , 56, 8657-8661	6.7	9
28	Thickness dependence of the strain, band gap and transport properties of epitaxial In2O3 thin films grown on Y-stabilised ZrO2(111). <i>Journal of Physics Condensed Matter</i> , 2011 , 23, 334211	1.8	38
27	Domain structure and optical property of epitaxial indium oxide film deposited on MgO(100) substrate. <i>Surface Science</i> , 2011 , 605, 977-981	1.8	9
26	Orientation dependent ionization potential of In2O3: a natural source for inhomogeneous barrier formation at electrode interfaces in organic electronics. <i>Journal of Physics Condensed Matter</i> , 2011 , 23, 334203	1.8	27
25	Thermodynamic stability, stoichiometry, and electronic structure of bcc-In2O3 surfaces. <i>Physical Review B</i> , 2011 , 84,	3.3	62
24	Influence of Al2O3 Buffer Layers on the Properties of IndiumII in Oxide Films on PET Substrate by RF-Magnetron Sputtering. <i>Materials Science Forum</i> , 2011 , 675-677, 1209-1212	0.4	
23	Surface structure of In2O3(111) (111) determined by density functional theory calculations and low energy electron diffraction. <i>Surface Science</i> , 2012 , 606, 1-6	1.8	20
22	Bulk and surface characterization of In2O3(001) single crystals. <i>Physical Review B</i> , 2012 , 85,	3.3	54
21	Domain Matching Epitaxial Growth of In2O3 Thin Films on 🖽 l2O3 (0001). <i>Crystal Growth and Design</i> , 2012 , 12, 1000-1007	3.5	48
20	Size-dependent shape and tilt transitions in In2O3 nanoislands grown on cubic Y-stabilized ZrO2(001) by molecular beam epitaxy. <i>ACS Nano</i> , 2012 , 6, 6717-29	16.7	18
19	Electrodeposition of In2O3 thin films from a dimethylsulfoxide based electrolytic solution. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 297-305	1.6	13

18	MBE of transparent semiconducting oxides. 2013 , 347-367		3
17	Composition-dependent electronic properties of indium linc Bxide elongated microstructures. <i>Acta Materialia</i> , 2013 , 61, 1932-1943	8.4	14
16	Macro- and microscopic properties of strontium doped indium oxide. <i>Journal of Applied Physics</i> , 2014 , 116, 043704	2.5	5
15	Effect of ion beam assisted deposition on the growth of indium tin oxide (ITO) nanowires. <i>CrystEngComm</i> , 2014 , 16, 4108-4112	3.3	14
14	Reducing the In2O3(111) Surface Results in Ordered Indium Adatoms. <i>Advanced Materials Interfaces</i> , 2014 , 1, 1400289	4.6	22
13	Dopant and Defect Induced Electronic States at In2O3 Surfaces. <i>Springer Series in Surface Sciences</i> , 2015 , 351-400	0.4	5
12	Structure and Optical Properties of Epitaxial Indium Oxide Films Deposited on Y-Stabilized ZrO2 (111) by MOCVD. <i>Journal of Electronic Materials</i> , 2015 , 44, 2719-2724	1.9	6
11	A novel surface modification scheme for ITO nanocrystals by acetylene: a combined experimental and DFT study. <i>Physical Chemistry Chemical Physics</i> , 2015 , 17, 26740-4	3.6	O
10	Pretreatment of ITO electrode and its physiochemical properties: Towards device fabrication. <i>Surface Engineering and Applied Electrochemistry</i> , 2016 , 52, 547-564	0.8	1
9	Effect of ITO surface properties on SAM modification: A review toward biosensor application. <i>Cogent Engineering</i> , 2016 , 3, 1170097	1.5	29
8	Structural and electron transport properties of single-crystalline In2O3 films compensated by Ni acceptors. <i>Applied Physics Letters</i> , 2017 , 111, 262103	3.4	3
7	Magnetic and plasmonic properties in noncompensated Fe-Sn codoped In2O3 nanodot arrays. <i>Applied Surface Science</i> , 2018 , 441, 415-419	6.7	9
6	Insight of DFT and ab initio atomistic thermodynamics on the surface stability and morphology of In2O3. <i>Applied Surface Science</i> , 2018 , 434, 1344-1352	6.7	30
5	Models of Surface Morphology and Electronic Structure of Indium Oxide and Indium Tin Oxide for Several Surface Hydroxylation Levels. <i>Journal of Physical Chemistry C</i> , 2018 , 122, 584-595	3.8	2
4	Combined pulsed laser deposition and non-contact atomic force microscopy system for studies of insulator metal oxide thin films. <i>Beilstein Journal of Nanotechnology</i> , 2018 , 9, 686-692	3	11
3	Interface Behaviour and Work Function Modification of Self-Assembled Monolayers on Sn-Doped In2O3. <i>Surfaces</i> , 2019 , 2, 241-256	2.9	1
2	In Situ Nanoscale Redox Mapping Using Tip-Enhanced Raman Spectroscopy. <i>Nano Letters</i> , 2019 , 19, 21	06£ 2 .51	3 42
1	Influence of Substrate Orientation and Oxygen Partial Pressure on the Morphology, Structure, and Electrical Property of Epitaxial Indium Tin Oxide Films. <i>Crystal Growth and Design</i> ,	3.5	O